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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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High Voltage Schottky Barrier Rectifier

Mar. 2008

### **General Description**

FMEN-230A is a High Voltage (100V) Schottky Barrier Diode, and has achieved low leakage current and low VF by selecting the best barrier metal.

### **Applications**

- •DC-DC converters
- •AC adapter
- High frequency rectification circuit

# Package TO220F(3Pin) 10.0 \$\phi 3.3\$ \$\phi \frac{\phi}{\phi} \f

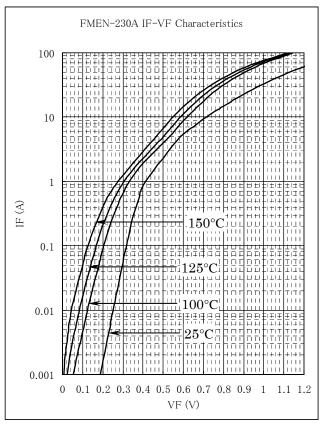
# **Key Specifications**

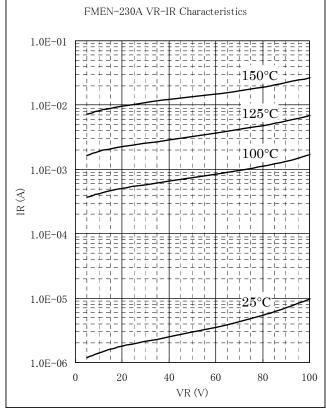
Symbol	Unit	Rating	Conditions
$V_{RM}$	V	100	
$V_{F}$	V	0.85	$I_F=15A$
I <sub>F(AV)</sub>	A	30	

# **Features**

- •High Voltage 100V guarantee
- Steady operation is possible even at the high temperature by the low leakage current.
- •Super-high speed & low noise switching.
- •Low forward voltage drop.

# **Typical Characteristics**





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# \* Absolute maximum ratings

No.	Parameter	Symbol	Unit	Rating	Conditions
1	1 Transient Peak Reverse Voltage		V	100	
2	2 Peak Reverse Voltage		V	100	
3	Average Forward Current	I <sub>F</sub> (AV)	A	30	
4	Peak Surge Forward Current	$I_{\mathrm{FSM}}$	A	150	Half sinewave, one shot
5	I²t Limiting Value	${ m I}^2{ m t}$	$ m A^2s$	112.5	1msec <t<10msec< td=""></t<10msec<>
6	Junction Temperature	Tj	°C	-40 to +150	
7	Storage Temperature	$T_{ m stg}$	°C	-40 to +150	

No.1, 2, 4&5 show ratings per one chip.

# **★** Electrical characteristics (Ta=25°C, unless otherwise specified)

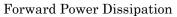
No.	Parameter	Symbol	Unit	Rating	Conditions
1	1 Forward Voltage Drop		V	0.85 max.	I <sub>F</sub> =15A
2	2 Reverse Leakage Current		uA	300 max.	$V_R = V_{RM}$
3	Reverse Leakage Current Under High Temperature	H•I <sub>R</sub>	mA	150 max.	V <sub>R</sub> =V <sub>RM</sub> , T <sub>j</sub> =150°C
4	Thermal Resistance	$R_{th(j\text{-}c)}$	°C/W	4.0 max.	Between Junction and case

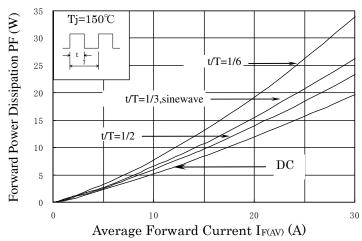
No.1, 2&3 show characteristics per one chip.

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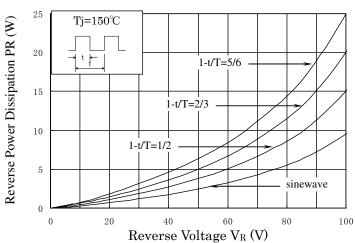
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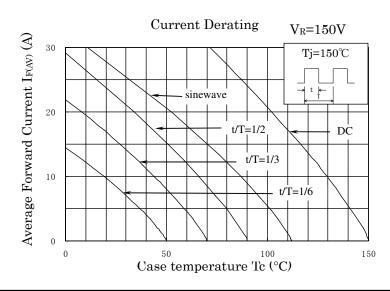
### \* Characteristics





# Reverse Power Dissipation

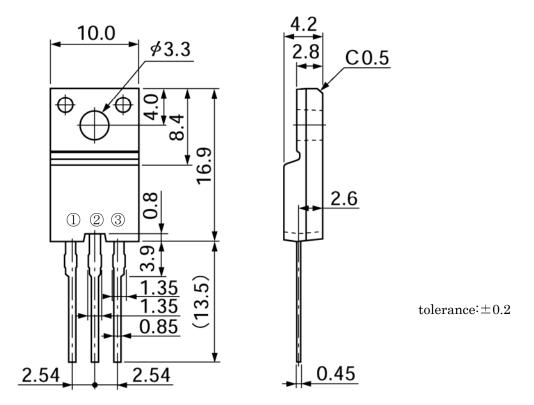




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# **★** Outline drawings, mm



# **\*** Connection Diagram

